

IN THE CLAIMS

Please cancel non-elected claims 3-5, without prejudice in view of the Restriction Requirement.

Please substitute the following amended claim(s) for corresponding claim(s) previously presented. A copy of the amended claim(s) showing current revisions is attached.

1. ~~(Amended) A semiconductor substrate device, comprising:~~
~~a first semiconductor substrate including a concave-convex surface; and~~
~~a second semiconductor substrate having a thin film insulator on a surface thereof,~~
~~wherein the first semiconductor substrate and the second semiconductor substrate~~
~~are brought together so that the concave-convex surface of the first semiconductor~~
~~substrate and the thin film insulator provided on the surface of the second semiconductor~~
~~substrate contact each other to form a cavity in the semiconductor substrate device.~~

Please add the following new claims:

6. ~~(New) A semiconductor substrate device, comprising:~~
~~a first semiconductor substrate including a concave-convex surface; and~~

a second semiconductor substrate having a thin film oxide insulator on a surface thereof, the surface of the second semiconductor substrate on which the thin film oxide insulator is provided being implanted with hydrogen ions,

wherein the first semiconductor substrate and the second semiconductor substrate are brought together so that the concave-convex surface of the first semiconductor substrate and the thin film oxide insulator provided on the ion implanted surface of the second semiconductor substrate contact each other to form a cavity in the semiconductor substrate device.

7. (New) A semiconductor substrate device, comprising:

a first semiconductor substrate including a concave-convex surface; and

a second semiconductor substrate having a thin film Si layer on a surface thereof,

wherein the first semiconductor substrate and the second semiconductor substrate are brought together so that the concave-convex surface of the first semiconductor substrate and the thin film Si layer provided on the second semiconductor substrate contact each other to form a cavity in the semiconductor substrate device.

8. (New) A semiconductor device according to claim 1, wherein the thin film insulator comprises a silicon oxide film.

9. (New) A semiconductor device according to claim 1, wherein the thin film insulator comprises a thin-film silicon layer.